# 2N3055AG (NPN), MJ15015G (NPN), MJ15016G (PNP)

# **Complementary Silicon High-Power Transistors**

These PowerBase complementary transistors are designed for high power audio, stepping motor and other linear applications. These devices can also be used in power switching circuits such as relay or solenoid drivers, dc–to–dc converters, inverters, or for inductive loads requiring higher safe operating area than the 2N3055.

### Features

• High Current-Gain - Bandwidth

MAXIMUM RATINGS (Note 1)

- Safe Operating Area
- These Devices are Pb-Free and are RoHS Compliant\*

Rating	Symbol	Value	Unit			
Collector–Emitter Voltage 2N3055AG MJ15015G, MJ15016G	V <sub>CEO</sub>	60 120	Vdc			
Collector–Base Voltage 2N3055AG MJ15015G, MJ15016G	V <sub>CBO</sub>	100 200	Vdc			
Collector–Emitter Voltage Base Reversed Biased 2N3055AG MJ15015G, MJ15016G	V <sub>CEV</sub>	100 200	Vdc			
Emitter-Base Voltage	V <sub>EBO</sub>	7.0	Vdc			
Collector Current – Continuous	Ι <sub>C</sub>	15	Adc			
Base Current	I <sub>B</sub>	7.0	Adc			
Total Device Dissipation (a) $T_C = 25^{\circ}C$ 2N3055AG MJ15015G, MJ15016G Derate above 25^C 2N3055AG MJ15015G, MJ15016G	P <sub>D</sub>	115 180 0.65 1.03	₩ ₩ ₩/°C			
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +200	°C			

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Indicates JEDEC Registered Data. (2N3055A)

## THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ ext{ heta}JC}$	1.52	0.98	°C/W

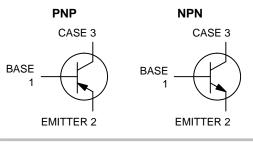
\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

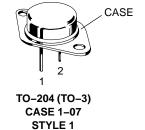


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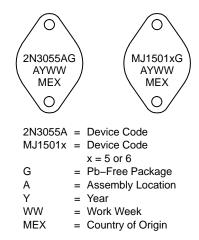
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## 15 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 60, 120 VOLTS – 115, 180 WATTS





### MARKING DIAGRAMS



### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

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## ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic			Min	Max	Unit
OFF CHARACTERISTICS (Note 2)					
Collector–Emitter Sustaining Voltage (Note 3) $(I_{C} = 200 \text{ mAdc}, I_{B} = 0)$	2N3055AG MJ15015G, MJ15016G	V <sub>CEO(sus)</sub>	60 120		Vdc
	2N3055AG MJ15015G, MJ15016G	I <sub>CEO</sub>	- -	0.7 0.1	mAdc
Collector Cutoff Current (Note 3) (V <sub>CEV</sub> = Rated Value, V <sub>BE(off)</sub> = 1.5 Vdc)	2N3055AG MJ15015G, MJ15016G	I <sub>CEV</sub>	-	5.0 1.0	mAdc
Collector Cutoff Current ( $V_{CEV}$ = Rated Value, $V_{BE(off)}$ = 1.5 Vdc, $T_{C}$ = 150°C)	2N3055AG MJ15015G, MJ15016G	I <sub>CEV</sub>		30 6.0	mAdc
Emitter Cutoff Current ( $V_{EB} = 7.0 \text{ Vdc}, I_C = 0$ )			-	5.0 0.2	mAdc
SECOND BREAKDOWN (Note 3)					
Second Breakdown Collector Current with Base Forward Biased (t = 0.5 s non-repetitive) 2N3055AG (V <sub>CE</sub> = 60 Vdc) MJ15015G, MJ15016G			1.95 3.0		Adc
ON CHARACTERISTICS (Note 2 and 3)					
$      DC Current Gain \\ (I_C = 4.0 Adc, V_{CE} = 2.0 Vdc) \\ (I_C = 4.0 Adc, V_{CE} = 4.0 Vdc) \\ (I_C = 10 Adc, V_{CE} = 4.0 Vdc) $		h <sub>FE</sub>	10 20 5.0	70 70 -	-
Collector-Emitter Saturation Voltage $(I_C = 4.0 \text{ Adc}, I_B = 400 \text{ mAdc})$ $(I_C = 10 \text{ Adc}, I_B = 3.3 \text{ Adc})$ $(I_C = 15 \text{ Adc}, I_B = 7.0 \text{ Adc})$		V <sub>CE(sat)</sub>	- - -	1.1 3.0 5.0	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = 4.0 Adc, V <sub>CE</sub> = 4.0 Vdc)			0.7	1.8	Vdc
DYNAMIC CHARACTERISTICS (Note 3)					
Current–Gain – Bandwidth Product (I <sub>C</sub> = 1.0 Adc, V <sub>CE</sub> = 4.0 Vdc, f = 1.0 MHz)	2N3055AG, MJ15015G MJ15016G	f <sub>T</sub>	0.8 2.2	6.0 18	MHz
Output Capacitance ( $V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz}$ )		C <sub>ob</sub>	60	600	pF
SWITCHING CHARACTERISTICS (2N3055AG o	nly) (Note 3)				
RESISTIVE LOAD					
Delay Time		t <sub>d</sub>	_	0.5	μs
Rise Time	$(V_{CC} = 30 \text{ Vdc}, I_{C} = 4.0 \text{ Adc},$	t <sub>r</sub>	_	4.0	μs
Storage Time	$\begin{split} I_{B1} = I_{B2} = 0.4 \text{ Adc}, \\ t_p = 25 \ \mu \text{s Duty Cycle} &\leq 2\% \end{split}$	ts	_	3.0	μs
Fall Time		t <sub>f</sub>	_	6.0	μS

Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤
 Indicates JEDEC Registered Data. (2N3055A)

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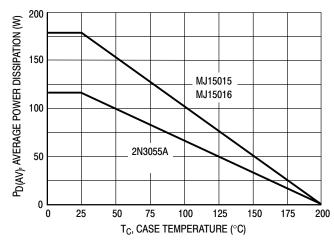
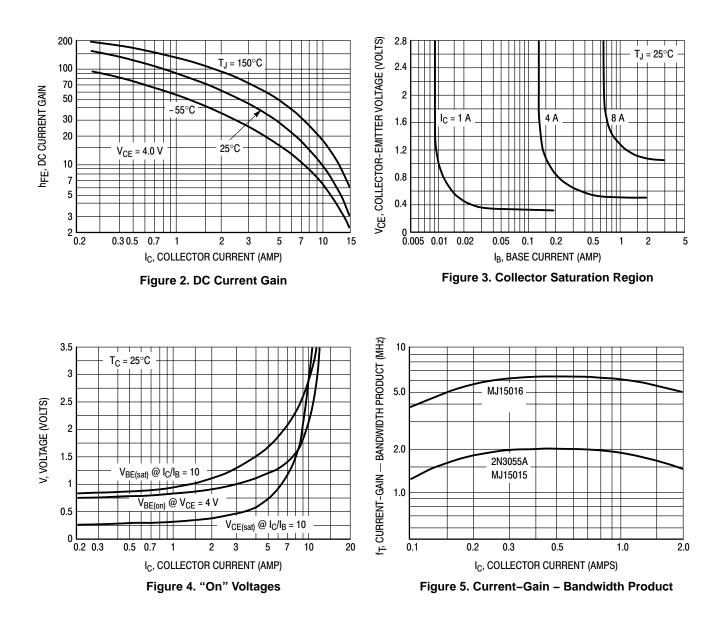


Figure 1. Power Derating



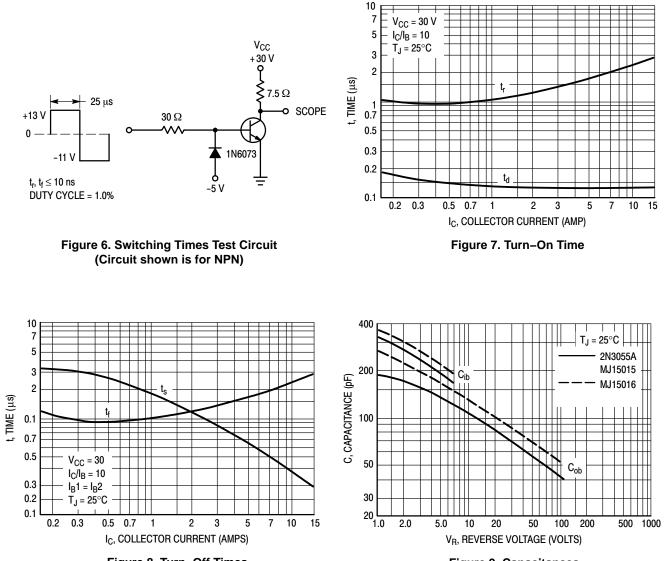
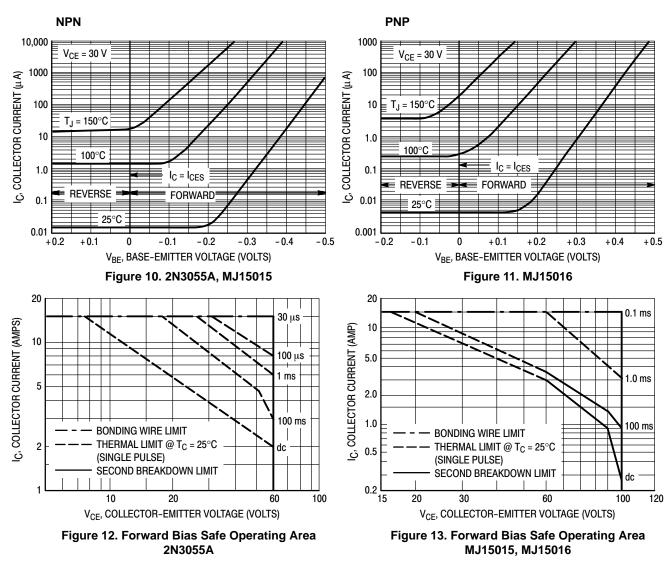


Figure 8. Turn-Off Times

Figure 9. Capacitances

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### **COLLECTOR CUT-OFF REGION**



There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe Operating area curves indicate  $I_C-V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 12 and 13 is based on  $T_C = 25^{\circ}C$ ;  $T_{J(pk)}$  is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated for temperature according to Figure 1.

#### **ORDERING INFORMATION**

Device	Package	Shipping
2N3055AG	TO-204 (Pb-Free)	100 Units / Tray
MJ15015G	TO-204 (Pb-Free)	100 Units / Tray
MJ15016G	TO-204 (Pb-Free)	100 Units / Tray

### MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



DIMENSIONS					,
SCALE 1:1	TO–204 (T CASE 1- ISSUE	-07		DATE 05/18/1988	3
$ \begin{array}{c}                                     $		2. 3.	ES: DIMENSIONING AND TOLE 714.5M, 1982. CONTROLLING DIMENSIO ALL RULES AND NOTES A REFERENCED TO-204AA <b>INCHES</b> DIM MIN MAX A 1.550 REF B 1.050 C 0.250 0.335 D 0.038 0.043 E 0.055 0.070 G 0.430 BSC H 0.215 BSC K 0.440 0.480 L 0.665 BSC N 0.830 Q 0.151 0.165 U 1.187 BSC V 0.131 0.188	DN: INCH. ASSOCIATED WITH	
PIN 1. BASE 2. EMITTER CASE: COLLECTOR STYLE 6:	STYLE 2: STYLE 3: PIN 1. BASE PIN 1. GAT 2. COLLECTOR 2. SOU CASE: EMITTER CASE: DRA STYLE 7: STYLE 8:	RCE 2. INPUT IN CASE: OUTPUT STYLE 9:	style 5: Pin 1. cathode 2. external Case: Anode		
PIN 1. GATE 2. EMITTER CASE: COLLECTOR	PIN 1. ANODE PIN 1. CATI 2. OPEN 2. CATI CASE: CATHODE CASE: ANO	HODE #2 2. ANODE #2	2		

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